

October 2014

# **FMMT549 PNP Low-Saturation Transistor**

### **Features**

- · This device is designed with high-current gain and low-saturation voltage with collector currents up to 2 A continuous.
- · Sourced from process PB.



1. Base 2. Emitter 3. Collector

# **Ordering Information**

Part Number	Marking	Package	Packing Method
FMMT549	549	SSOT 3L	Tape and Reel

## Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at  $T_A$  = 25°C unless otherwise noted.

Symbol	Parameter		Value	Unit	
V <sub>CEO</sub>	Collector-Emitter Voltage		-30	V	
V <sub>CBO</sub>	Collector-Base Voltage		-35	V	
V <sub>EBO</sub>	Emitter-Base Voltage		-5	V	
I <sub>C</sub>	Collector Current	Continuous	-1	A	
		Peak Pulse Current	-2		
TJ	Junction Temperature		150	°C	
T <sub>STG</sub>	Storage Temperature Range		-55 to +150	°C	

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

## **Thermal Characteristics**

Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Max.	Unit
P <sub>D</sub>	Total Device Dissipation, by R <sub>θJA</sub>	500	mW
	Derate Above 25°C	4	mW/°C
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	250	°C/W

### Note:

3. Device is mounted on FR-4 PCB 4.5 inch X 5 inch, mounting pad 0.02 in<sup>2</sup> of 2 oz copper.

## **Electrical Characteristics**

Values are at  $T_A = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = -10 mA, I <sub>B</sub> = 0	-30		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_C = -100  \mu A, I_E = 0$	-35		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = -100 μA, I <sub>C</sub> = 0	-5.0		V
Ісво	Collector Cut-Off Current	$V_{CB} = -30 \text{ V}, I_{E} = 0$		-100	nA
		$V_{CB} = -30 \text{ V}, I_{E} = 0,$ $T_{A} = 100^{\circ}\text{C}$		-10	μА
I <sub>EBO</sub>	Emitter Cut-Off Current	$V_{EB} = -4.0 \text{ V}, I_{C} = 0$		-100	nA
	DC Current Gain <sup>(4)</sup>	$V_{CE} = -2.0 \text{ V}, I_{C} = -50 \text{ mA}$	70		
h <sub>FE</sub>		$V_{CE}$ = -2.0 V, $I_{C}$ = -500 mA	100	300	
		V <sub>CE</sub> = -2.0 V, I <sub>C</sub> = -1 A	80		
		V <sub>CE</sub> = -2.0 V, I <sub>C</sub> = -2 A	40		
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage <sup>(4)</sup>	$I_C = -1 \text{ A}, I_B = -100 \text{ mA}$		-500	mV
		$I_C = -2 \text{ A}, I_B = -200 \text{ mA}$		-750	1110
V <sub>BE</sub> (sat)	Base-Emitter Saturation Voltage <sup>(4)</sup>	$I_C = -1 \text{ A}, I_B = -100 \text{ mA}$		-1.25	V
V <sub>BE</sub> (on)	Base-Emitter On Voltage <sup>(4)</sup>	I <sub>C</sub> = -1 A, V <sub>CE</sub> = -2.0 V		-1.0	V
f <sub>T</sub>	Current Gain Bandwidth Product	I <sub>C</sub> = -100 mA, V <sub>CE</sub> = -5 V, f = 100 MHz	100		MHz
C <sub>obo</sub>	Output Capacitance	V <sub>CB</sub> = -10 V, I <sub>E</sub> = 0, f = 1 MHz		25	pF

### Note:

4. Pulse test: pulse width  $\leq$  300  $\mu$ s, duty cycle  $\leq$  2.0%

# **Typical Performance Characteristics**

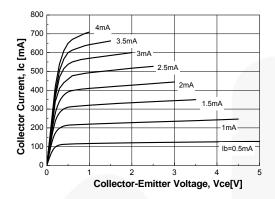


Figure 1. Collector-Emitter Voltage vs.
Collector Current

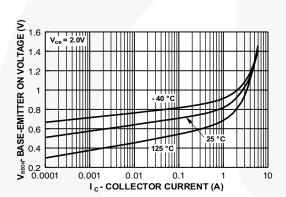


Figure 4. Base-Emitter On Voltage vs.
Collector Current

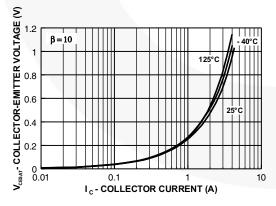


Figure 5. Collector-Emitter Saturation Voltage vs.
Collector Current

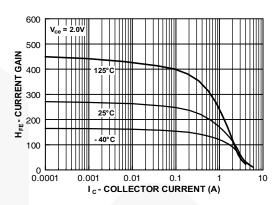


Figure 2. Current Gain vs. Collector Current

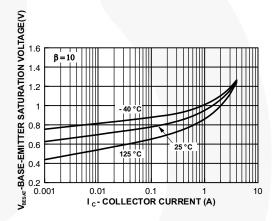


Figure 5. Base-Emitter Saturation Voltage vs. Collector Current

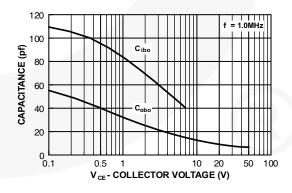


Figure 6. Input / Output Capacitance vs.
Reverse Bias Voltage

3

# **Physical Dimensions** 0.95 2.92±0.12-A 3 В 1.40 1.40±0.12 2.20 2 (0.29)--1.00◆ 0.20M A B 0.95 -1.90 -1.90 LAND PATTERN RECOMMENDATION SEE DETAIL A--1.12 MAX 0.10 (0.94)△ 0.10M C C $2.51\pm0.20$ GAGE PLANE NOTES: UNLESS OTHERWISE SPECIFIED 0.20 NO JEDEC REFERENCE AS OF AUGUST 2003 ALL DIMENSIONS ARE IN MILLIMETERS. DIMENSIONS ARE EXCLUSIVE OF BURRS, MOLD FLASH AND TIE BAR EXTRUSIONS. DIMENSIONING AND TOLERANCING PER ASME Y14.5M — 1994. 0.43 0.33 SEATING PLANE (0.56)DETAIL A SCALE: 50:1 MA03BREVB

Figure 7. MOLDED PACKAGE, SUPERSOT, 3-LEAD





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Definition of Terms			
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